

Workshop FAME III (Fundamentals and Advances of MOVPE processes)

22-13th June 2025, GreEn-ER building, 21 Avenue des Martyrs, Grenoble

Thursday - June 12th			
8h30-9h00	Welcome (no beverages or food)		
9h00	Welcome speech of the FAME III workshop by Christophe Durand		
SESSION 1 chaired by Emanuele Pelucchi			
9h05	Rachel Oliver University of Cambridge	LED applications of electrochemical sub-surface porosification of nitrides	
9h40	David Lackner Fraunhofer ISE	III-V semiconductors for solar cells	
10h15 - 10h45	Coffee break		
SESSION 2 chaired by Christoph Margenfeld			
10h45	Kerstin Voltz University of Marburg	Challenges in MOCVD growth of III-chalcogenides	
11h20	Pierre-Marie Coulon CRHEA (Univ. Côte d'Azur/CNRS)	A novel approach to grow thick relaxed crack free AlGaN on GaN for ultraviolet microdevice	
11h55	Moritz Brehm JKU (J. Kepler University)	Epitaxy of group-IV materials by LT-MBE	
12h30 - 13h30	Lunch offered by Aixtron		
Sponsor short presentations			
13h30	Gerbert De Kok	Nouryon	Precursors by Nouryon
13h40	Laurent Cuzin	Isère Froid	Solution for thermal baths by Isère froid
13h50	Thilo Hepp	Dockweiler Chemicals	Rare Earth Precursors by Dockweiler
SESSION 3 chaired by Matthew Charles			
14h00	Michael Heuken Aixtron	Recent progress and future trends in industrial Metalorganic Vapour Phase Epitaxy	
14h35	Irène Mangiano Clavero TU Braunschweig	Epitaxy of Three-Dimensional GaN Microstructures: Challenges and Prospects	
15h10	Francesco Montalenti University of Milano-Bicocca	ML-enabled boosting of growth simulations	
15h45 - 16h45	Poster session with local beers and refreshments		
16h45 - 18h	Lab visits or free visit of Grenoble		
18h30-22h30	18h30 - 19h15 : Visit of Glénat Museum in the Couvent St Cécile (37 rue Servan, Grenoble)		
	19h15-22h30 : Workshop dinner at "Les Jardins de St Cécile" (18 rue de l'Alma, Grenoble)		

Friday - June 13th		
8h15-8h30	Welcome (no beverages or food)	
SESSION 1 chaired by Menno Kappers		
8h30	Amélie Dussaigne CEA - LETI	Red emitting InGaN QWs grown on InGaN based micro/nano-structures for full color micro-display
9h05	Benjamin Groven IMEC	Nucleation and growth of CVD group-VI transition metal disulfides: the M(CO) ₆ and H ₂ S system
9h40	Suresh Sundaram Georgia Tech Europe	MOVPE growth of Boron Nitride
10h15 - 10h45	Coffee break	
SESSION 2 chaired by Joël Eymery		
10h45	Nicolas Grandjean EPFL	Point defects in nitrides
11h20	Davide Colucci IMEC	Deterministic single photon source based on GaAs nano-ridge engineering on silicon
11h55	Maksym Myronov University of Warwick	Heteroepitaxy of high mobility SiGe 2D systems
12h30 - 13h30	Lunch offered by Aixtron + committee meeting	
SESSION 3 chaired by Blandine Alloing and Yves Mols		
13h30	Erik Bakkers TU/e Eindhoven	Hexagonal SiGe growth
14h05	Jérôme Napierala Aledia	Nanowires based μ LEDs on Silicon for display application
14h40	Simone Assali CEA - PHÉLIQS	Engineering SiGeSn photonics and quantum materials
15h15	Pietro Pampili Tyndall National Institute	Growth of N-polar nitrides
15h50-16h	Closing speech	

Poster session - Thursday June 12th - from 3.45 to 4.45 pm

IV-group Semiconductors

1	Denny Lamon	TU/e Eindhoven	Growth of Hexagonal SiGe Quantum Structures
2	Léa Combes	CEA - Pheliqs	Selective area growth of Infrared GeSn semiconductors on Si
3	Mathieu Turmel	CEA - Pheliqs	Tailoring novel group IV quantum materials
4	Andrea Fantasia	University of Milano-Bicocca	Exploring Pressure-Dependent Kinetics of Phase Transitions in Si and Ge Using ML Interatomic Potentials
5	Enrique Prado Navarrete	Johannes Kepler University	Ultra-Low Temperature MBE Growth of (Si)Ge Nanosheets for Advanced Nanoelectronic Applications
6	Veronica Regazzoni	Università di Milano Bicocca	Electronic Properties of Extended Defects in Germanium

III-N Nitride Semiconductors

7	Jonathan Henriques	CEA - Pheliqs	Selective area growth of GaN micro-platelets on graphene for micro-LEDs applications
8	Hassan Damen	CEA - Leti	High In content InGaIn donor and regrowth on porous InGaIn
9	Marcel Kröner	Philipps University Marburg	Low temperature MOVPE of Sc, Y and La containing (B,Al,Ga)N alloys
10	Thi May Tran	Georgia Tech Europe	Transferrable GaN-based Micro-LEDs heterostructures grown on h-BN for optogenetic applications

III-V group Semiconductors

11	Christoph Klein	Fraunhofer ISE	Metalorganic Vapor-Phase Epitaxy Growth of Al _x Ga _{1-x} As with Deposition Rates above 50 µm/h
12	Yves Mols	IMEC	Challenges in GaAsSb growth on InP
13	Rémy Tribout	LTM (CNRS - UGA)	III-V Epitaxy on 300mm Si Substrate by MOCVD for Micro- and Opto-electronic Applications
14	Swati Mukherjee	Tyndall National Institute	Exploring droplet-epitaxy nanostructures in MOVPE for telecom wavelength
15	Akanksha Kapoor	PITC InP-Program TU/e	InP epitaxy for Photonic Integrated Circuits (PICs)
16	Krzysztof Klos	www.Photin.eu	Self-Organized Natural Superlattices in MOVPE of InAsSbP

Ultra-Wide Band Gap Semiconductors

17	Christoph Margenfeld	TU Braunschweig	Epitaxy of Ultra-Wide Band Gap AlGaIn on High-Temperature Annealed AlN Templates
18	Andy Seguret	LMGP / CEA-Pheliqs	ALD of epitaxial Ga ₂ O ₃ thin films
19	Houssein Mohaidly	CEA - Pheliqs	From UV-B to UV-C emission in core-shell structures based on (Al)GaIn-µpillars arrays

2D materials

20	Vishnu Ottapilakkal	Georgia Tech Europe	Selective Epitaxial Growth of High-quality hBN on Micron-Sized Epigraphene Patterns via MOVPE
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FAME III

3rd workshop: "Fundamentals and Advances of MOVPE processes"

12th - 13th June 2025

Auditorium Bergès at the GrEn-ER building
21 Avenue des Martyrs Grenoble, France

Nouryon

Dock

AIxTRON

Aledia
Innovative displays

LAYTEC

cea

GRENOBLE ALPES
MÉTROPOLE

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